Unit: mm

2SB0941, 2SB0941A (2SB941, 2SB941A)

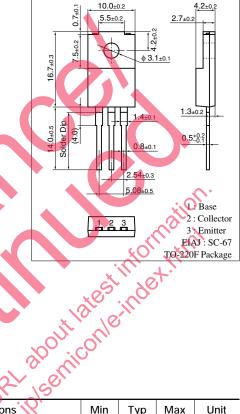
Silicon PNP epitaxial planar type

For low-frequency power amplification

Complementary to 2SD1266 and 2SD1266A

- Features
- \bullet High forward current transfer ratio h_{FE} which has satisfactory linearity
- Low collector to emitter saturation voltage V_{CE(sat)}
- Full-pack package which can be installed to the heat sink with one screw

Absolute Maximum Ratings $T_{C} = 25^{\circ}C$								
Parameter		Symbol	Rating	Unit				
Collector to base	2SB0941	V _{CBO}	-60	V				
voltage	2SB0941A		-80					
Collector to	2SB0941	V _{CEO}	-60	V				
emitter voltage	2SB0941A		-80					
Emitter to base voltage		V _{EBO}	-5	V				
Peak collector current		I _{CP}	-5	А				
Collector current		I_{C}	-3	A				
Collector power	$T_C = 25^{\circ}C$	P _C	35	W				
dissipation	$T_a = 25^{\circ}C$		2					
Junction temperature		Tj	150	°C				
Storage temperature		T _{stg}	-55 to +150	°C				

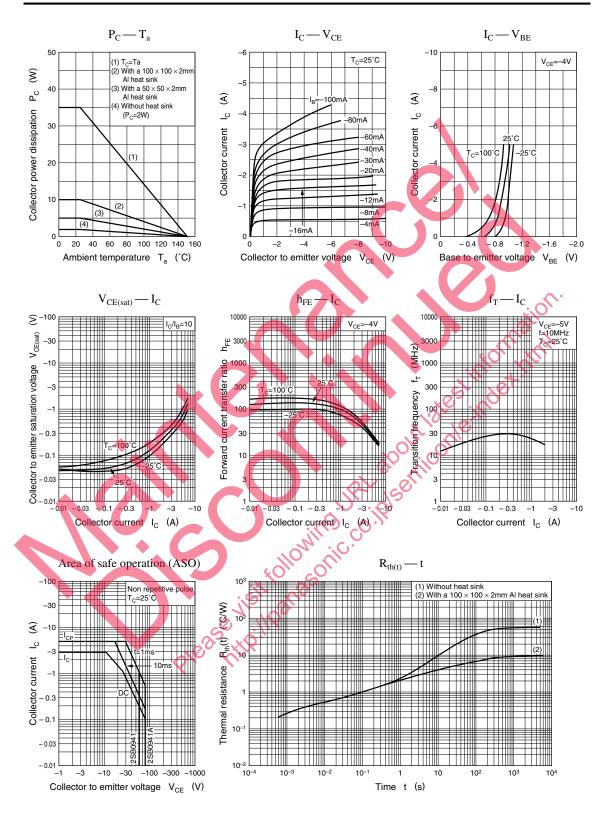


Electrical Characteristics $T_c = 25^{\circ}C$

Parameter	S <mark>ym</mark> bol	Conditions	Min	Тур	Max	Unit
Collector cutoff 2SB0941	I _{CES}	$V_{CE} = -60$ V, $V_{BE} = 0$			-200	μΑ
current 2SB0941A		$V_{CE} = -80 \text{ V}, \text{V}_{BE} = 0$			-200	
Collector cutoff 2SB0941	I _{CEO}	$V_{CE} = -30 \text{ V}, J_{B} = 0$			-300	μΑ
current 2SB0941A		$V_{CE} = -60 \text{ V}, I_{B} = 0$			-300	
Emitter cutoff current	I _{EBO}	$V_{EB} = -5 \text{ V}, \text{ I}_{\text{C}} = 0$			-1	mA
Collector to emitter 2SB0941	or to emitter 2SB0941 V_{CPO} $I_C = -30 \text{ mA}, I_B = 0$		-60			v
voltage 2SB0941A	en xx	<u>R</u>	-80			
Forward current transfer ratio	h _{FE1} *	$V_{CE} = -4 V, I_C = -1 A$	70		250	
	h _{FE2}	$V_{CE} = -4 V, I_C = -3 A$	10			
Base to emitter voltage		$V_{CE} = -4 V, I_C = -3 A$			-1.8	V
Collector to emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -3$ A, $I_{\rm B} = -0.375$ A			-1.2	V
Transition frequency f		$V_{CE} = -10 \text{ V}, I_{C} = -0.5 \text{ A}, f = 10 \text{ MHz}$		30		MHz
Turn-on time	t _{on}	$I_{C} = -1 \text{ A}, I_{B1} = -0.1 \text{ A}, I_{B2} = 0.1 \text{ A}$		0.5		μs
Storage time	t _{stg}			1.2		μs
Fall time	t _f			0.3		μs

Rank Q Ρ 70 to 150 120 to 250 h_{FE1}

Note.) The Part numbers in the Parenthesis show conventional part number.



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